

REMARKS

Claims 1-8 are pending. By this Amendment, the specification is amended.

Furthermore, claim 1 is amended to better distinguish over the prior art. Reconsideration is respectfully requested.

It is gratefully appreciated that the Office Action indicates that claims 2 and 6-8 are allowed.

The Office Action rejects claims 1, 4 and 5 under 35 U.S.C. 103(a) as being unpatentable over Hayashi (U.S. Publication No. 2003/0197598) in view of Brown (U.S. Patent No. 6,417,526) and Streetman ("Solid State Electronic Devices," p. 205); claim 3 is rejected under 35 U.S.C. 103(a) over Hayashi, Brown, Streetman and Kanbara (U.S. Patent No. 4,575,925). The rejections are respectfully traversed.

In particular, the applied references do not disclose or suggest a semiconductor device, including at least a p-type silicon layer including implanted germanium, as recited in independent claim 1.

Specifically, Hayashi discloses a contact list IC card 1 that includes a semiconductor integrated circuit 2.

Brown discloses in Fig. 1 a semiconductor body 10 that includes a p-conductivity region which includes a mixed crystal of silicon and germanium. See col. 5, lines 25-35.

Streetman discloses solid state electronic devices including switching diodes.

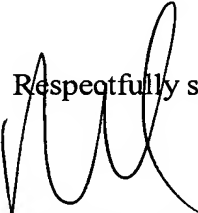
In contrast to the claimed invention, the applied references do not disclose or suggest a semiconductor device, including at least a p-type silicon layer including implanted germanium. On the contrary, nowhere in the applied references are these features disclosed or suggested. In fact, the Office Action admits that the prior art does not disclose or suggest a fabrication process for a semiconductor device which contains a diode that has a p-type

silicon-germanium mixed crystal layer (attained by ion implanting germanium into silicon) and an n-type silicon layer junction to the p-type silicon-germanium mixed crystal layer.

Thus, claims 1 and 3-5 are in condition for allowance. Accordingly, it is respectfully requested that the rejections under 35 U.S.C. 103(a) be withdrawn.

In view of the foregoing, this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 1 and 3-5 are earnestly solicited.

Should the Examiner believe that anything further is desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicant's attorney at the telephone number listed below.

Respectfully submitted,

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